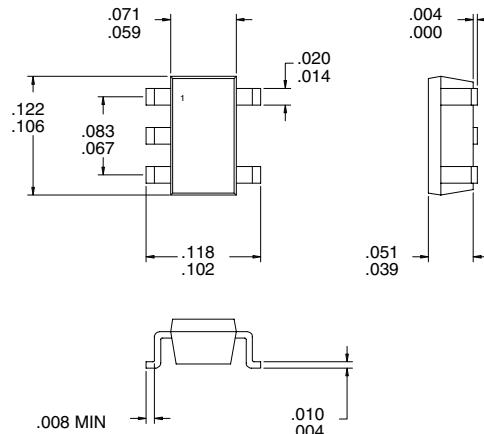


Typical Applications

- Broadband Gain Blocks
- Final PA for Low-Power Applications
- IF or RF Buffer Amplifiers
- Driver Stage for Power Amplifiers
- Oscillator Loop Amplifiers

Product Description

The RF2326 is a general purpose, low-cost silicon amplifier designed for operation from a 3V supply. The Darlington circuit configuration with resistive feedback allows for broadband cascadable amplification. The device is unconditionally stable and internally matched to 50Ω . The only external components required for specified performance are bypass and DC blocking capacitors and two bias elements (as shown in application schematic). The RF2326 is available in a very small industry-standard SOT-23 5-lead surface mount package, enabling compact designs which conserve board space.

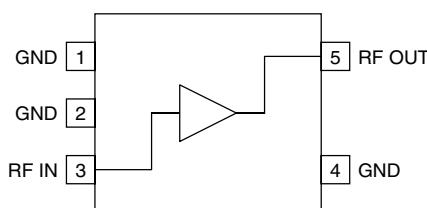


4

GENERAL PURPOSE
AMPLIFIERS

Optimum Technology Matching® Applied

- | | | |
|--------------------------------------------|-----------------------------------|--------------------------------------|
| <input checked="" type="checkbox"/> Si BJT | <input type="checkbox"/> GaAs HBT | <input type="checkbox"/> GaAs MESFET |
| <input type="checkbox"/> Si Bi-CMOS | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si CMOS |



Functional Block Diagram

Package Style: SOT-23-5

Features

- DC to >2000 MHz Operation
- 2.7V to 3.3V Single Supply
- +18 dBm Output IP3
- 12dB Gain at 900MHz
- 10dB Gain at 1900MHz
- Internally 50Ω Matched Input and Output

Ordering Information

RF2326 3V General Purpose Amplifier
RF2326 PCBA Fully Assembled Evaluation Board

RF Micro Devices, Inc.
7625 Thorndike Road
Greensboro, NC 27409, USA

Tel (336) 664 1233
Fax (336) 664 0454
<http://www.rfmd.com>

Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	4.0	V
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C

**Caution!** ESD sensitive device.

RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

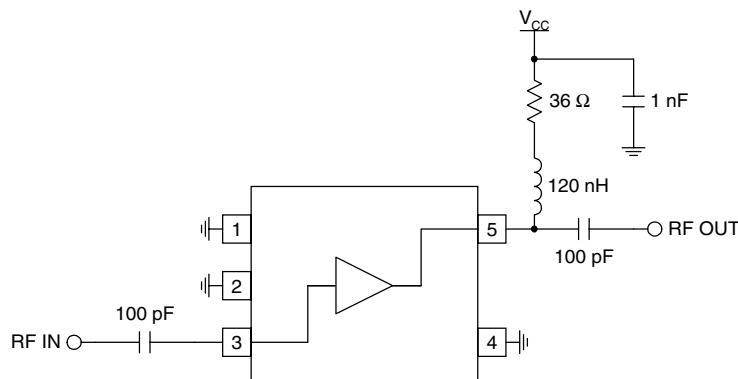
4

GENERAL PURPOSE AMPLIFIERS

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Overall					T=27 °C, V _{CC} =3.0V
Frequency Range		DC to >2000		MHz	
100MHz Performance					T=27 °C, V _{CC} =3.0V
Gain		12		dB	
Noise Figure		5.9		dB	
Output IP3		19		dBm	
Output P _{1dB}		7		dBm	
Input Return Loss		13		dB	
Output Return Loss		13		dB	
Isolation		18		dB	
500MHz Performance					T=27 °C, V _{CC} =3.0V
Gain		13		dB	
Noise Figure		5.9		dB	
Output IP3		19		dBm	
Output P _{1dB}		8		dBm	
Input Return Loss		15		dB	
Output Return Loss		27		dB	
Isolation		17		dB	
900MHz Performance	10.6	12	13.5	dB	T=27 °C, V _{CC} =3.0V
Gain		5.7		dB	
Noise Figure		18		dBm	
Output IP3		7		dBm	
Output P _{1dB}		12		dB	
Input Return Loss		21		dB	
Output Return Loss		18		dB	
1000MHz Performance					T=27 °C, V _{CC} =3.0V
Gain		12		dB	
Noise Figure		5.8		dB	
Output IP3		17		dBm	
Output P _{1dB}		6		dBm	
Input Return Loss		11		dB	
Output Return Loss		20		dB	
Isolation		18		dB	
2000MHz Performance					T=27 °C, V _{CC} =3.0V
Gain		10		dB	
Noise Figure		5.8		dB	
Output IP3		13		dBm	
Output P _{1dB}		4		dBm	
Input Return Loss		9		dB	
Output Return Loss		16		dB	
Isolation		18		dB	
Power Supply					
Operating Voltage	24.6	3.0±10%		V	
Operating Current		25	28.7	mA	V _{CC} =3.0V

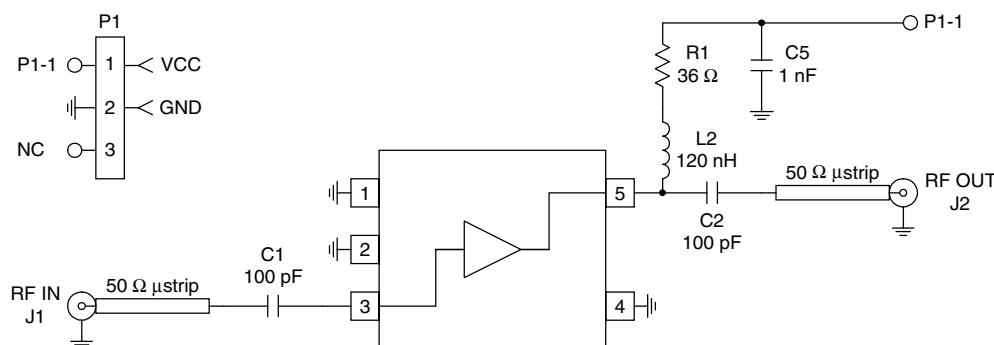
Pin	Function	Description	Interface Schematic
1	GND	Ground connection. Keep traces physically short and connect immediately to ground plane for best performance.	
2	GND	Same as pin 1.	
3	RF IN	RF input pin. This pin is not externally DC blocked and thus requires an external blocking capacitor suitable for the frequency of operation. The input impedance of this pin is internally matched to 50Ω using resistive feedback.	
4	GND	Same as pin 1.	
5	RF OUT	RF output and bias pin. The input impedance of this pin is internally matched to 50Ω using resistive feedback. Bias should be supplied to this pin through an external series resistor and RF choke inductor. Because DC biasing is present on this pin, a DC blocking capacitor should be used in most applications (see application schematic). The supply side of the bias network should be well-bypassed.	See pin 3 schematic.

Application Schematic

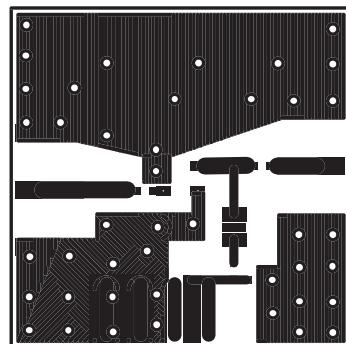
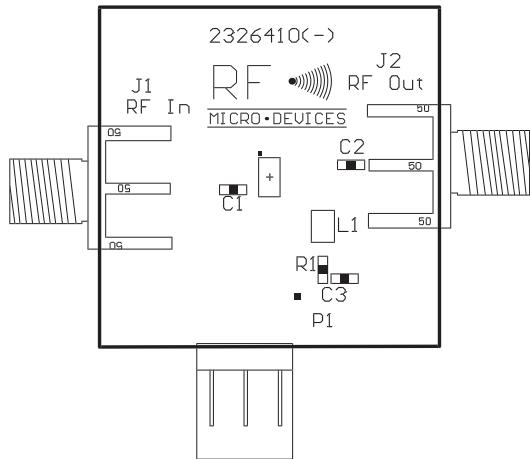


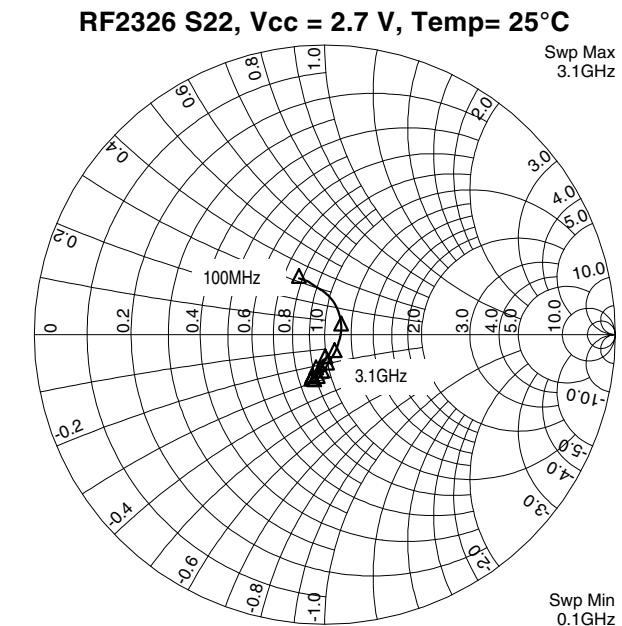
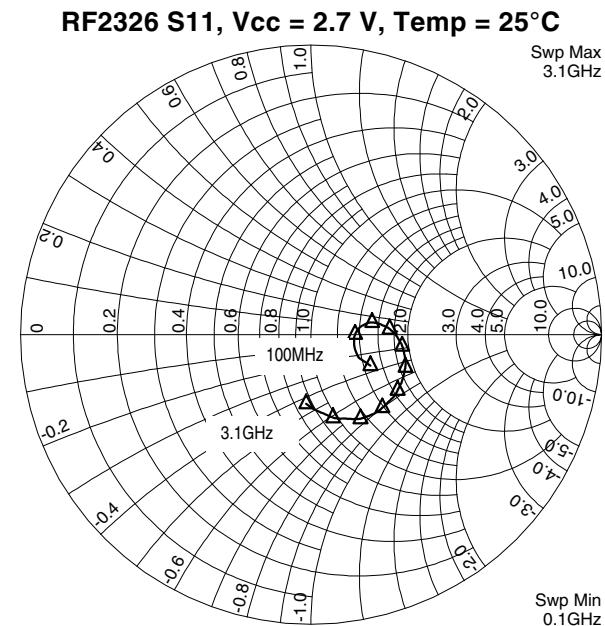
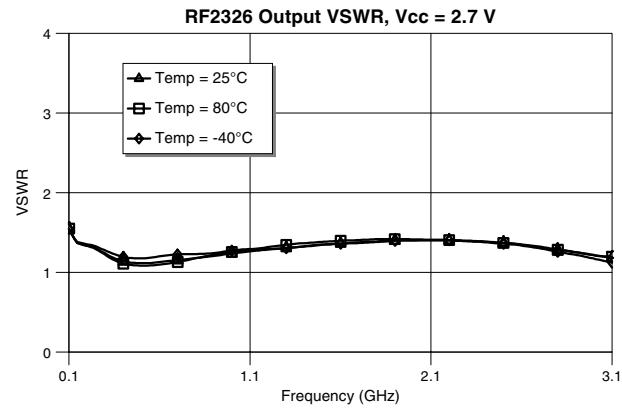
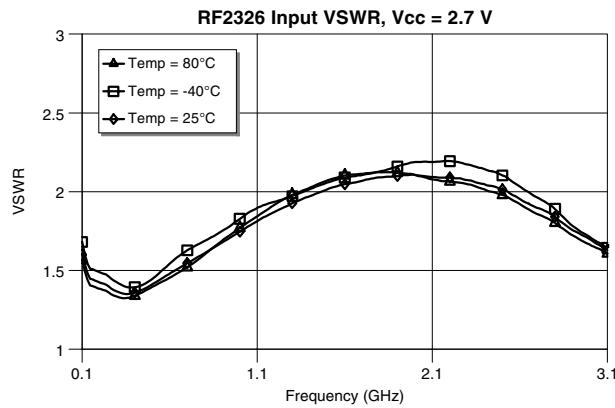
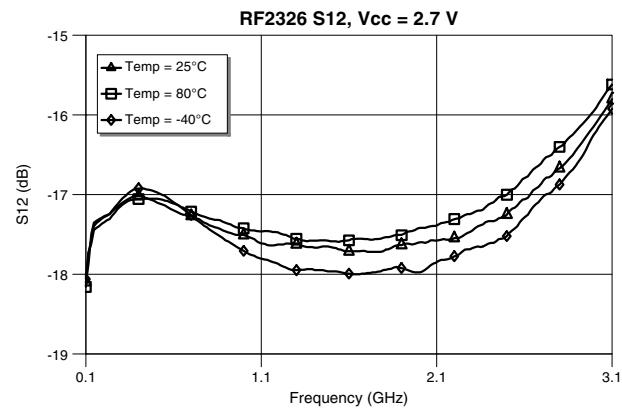
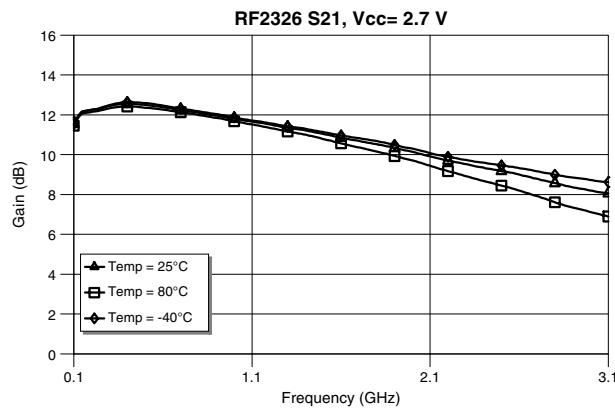
Evaluation Board Schematic

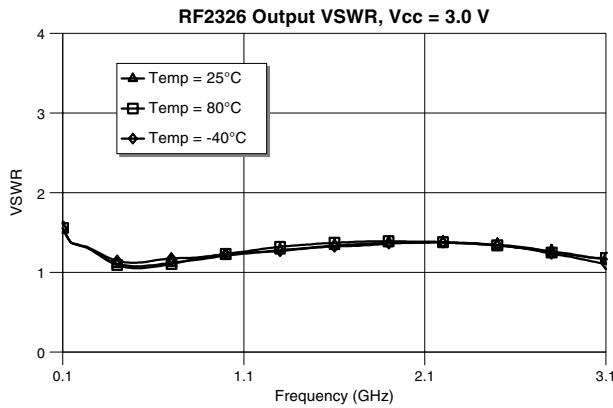
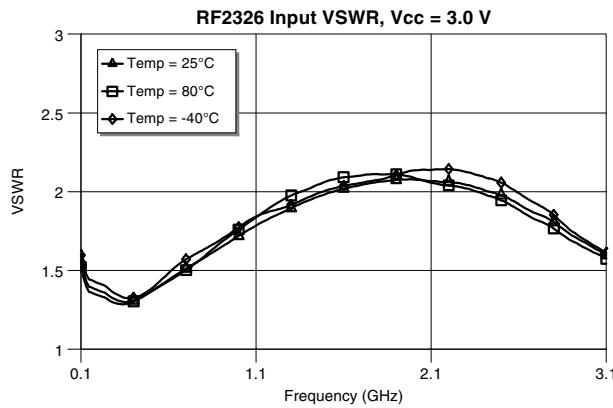
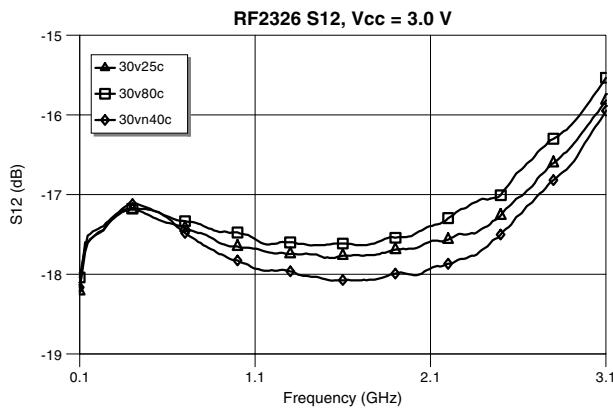
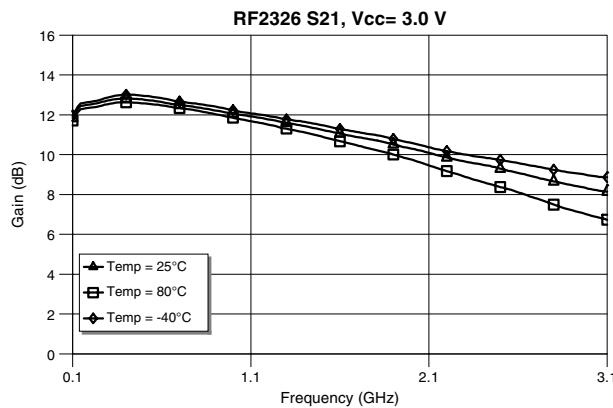
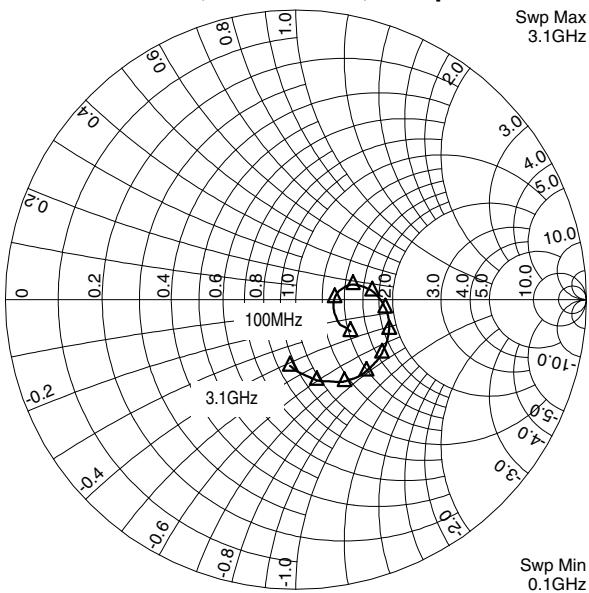
(Download [Bill of Materials](#) from www.rfmd.com.)



Evaluation Board Layout 1" x 1"





**RF2326 S11, V_{cc} = 3.0 V, Temp = 25°C****RF2326 S22, V_{cc} = 3.0 V, Temp = 25°C**